

Silicon PNP Power Transistors

2N3791 2N3792

DESCRIPTION

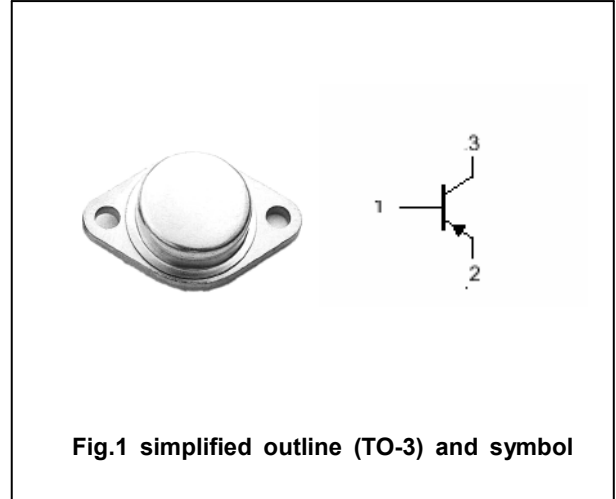
- With TO-3 package
- Complement to type 2N3715 ,2N3716
- Excellent safe operating area

APPLICATIONS

Designed for medium-speed switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N3791	-60	V
		2N3792	-80	
V_{CEO}	Collector-emitter voltage	2N3791	-60	V
		2N3792	-80	
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-10	A
I_B	Base current		-4	A
P_D	Total Power Dissipation	$T_C=25^\circ\text{C}$	150	W
T_j	Junction temperature		200	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{(th)jc}$	Thermal resistance junction to case	1.17	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N3791	I _C =-0.2A ; I _B =0	-60			V
		2N3792		-80			V
V _{CE(sat)}	Collector-emitter saturation voltage		I _C =-5A; I _B =-0.5A			-1.0	V
V _{BE(on)-1}	Base-emitter on voltage		I _C =-5A ; V _{CE} =-2V			-1.8	V
V _{BE(on)-2}	Base-emitter on voltage		I _C =-10A ; V _{CE} =-4V			-4.0	V
I _{CEX}	Collector cut-off current	2N3791	V _{CE} =-60V; V _{BE(off)} =-1.5V T _C =150°C			-1.0 -5.0	mA
		2N3792	V _{CE} =-80V; V _{BE(off)} =-1.5V T _C =150°C			-1.0 -5.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =-7V; I _C =0			-5.0	mA
h _{FE-1}	DC current gain		I _C =-1A ; V _{CE} =-2V	50		180	
h _{FE-2}	DC current gain		I _C =-3A ; V _{CE} =-2V	30			
f _T	Transition frequency		I _C =-0.5A; V _{CE} =-10V	4			MHz

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PACKAGE OUTLINE

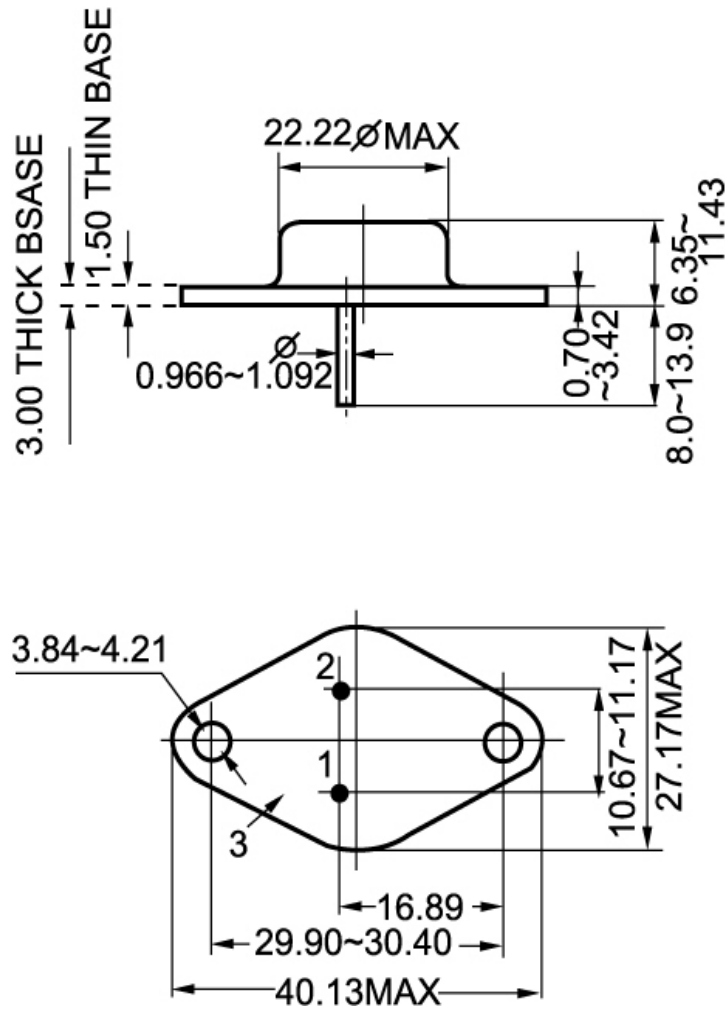


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)